

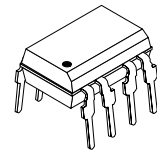
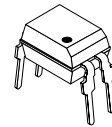
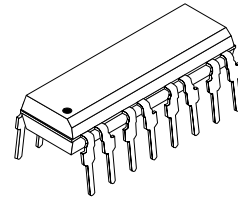


Optocoupler with Phototransistor Output

Description

The TCET110./ TCET2100/ TCET4100 consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 4-lead up to 16-lead plastic dual inline package.

The elements are mounted on one leadframe using a **coplanar technique**, providing a fixed distance between input and output for highest safety requirements.



14925

Applications

Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):

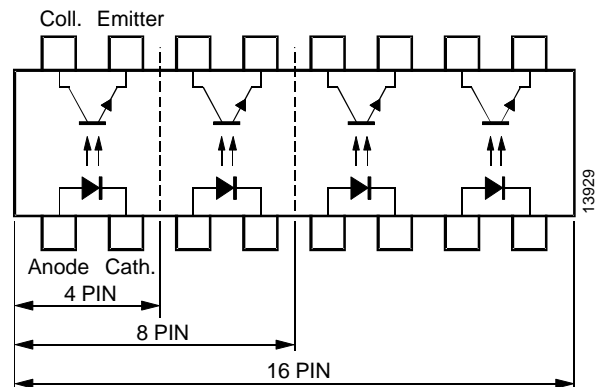
- For appl. class I – IV at mains voltage $\leq 300\text{ V}$
- For appl. class I – III at mains voltage $\leq 600\text{ V}$ according to VDE 0884, table 2, suitable for:

Switch-mode power supplies, line receiver, computer peripheral interface, microprocessor system interface.

VDE Standards

These couplers perform safety functions according to the following equipment standards:

- **VDE 0884**
Optocoupler for electrical safety requirements
- **IEC 950/EN 60950**
Office machines (applied for reinforced isolation for mains voltage $\leq 400\text{ V}_{\text{RMS}}$)
- **VDE 0804**
Telecommunication apparatus and data processing
- **IEC 65**
Safety for mains-operated electronic and related household apparatus



0884

Order Instruction

| Ordering Code | CTR Ranking | Remarks |
|-----------------------------------|-------------|------------------------|
| TCET1100/ TCET1100G ¹⁾ | 50 to 600% | 4 Pin = Single channel |
| TCET1101/ TCET1101G ¹⁾ | 40 to 80% | 4 Pin = Single channel |
| TCET1102/ TCET1102G ¹⁾ | 63 to 125% | 4 Pin = Single channel |
| TCET1103/ TCET1103G ¹⁾ | 100 to 200% | 4 Pin = Single channel |
| TCET1104/ TCET1104G ¹⁾ | 160 to 320% | 4 Pin = Single channel |
| TCET1105/ TCET1105G ¹⁾ | 50 to 150% | 4 Pin = Single channel |
| TCET1106/ TCET1106G ¹⁾ | 100 to 300% | 4 Pin = Single channel |
| TCET1107/ TCET1107G ¹⁾ | 80 to 160% | 4 Pin = Single channel |
| TCET1108/ TCET1108G ¹⁾ | 130 to 260% | 4 Pin = Single channel |
| TCET1109/ TCET1109G ¹⁾ | 200 to 400% | 4 Pin = Single channel |
| TCET2100 | 50 to 600% | 8 Pin = Dual channel |
| TCET4100 | 50 to 600% | 16 Pin = Quad channel |

¹⁾ G = Leadform 10.16 mm; G is not marked on the body

Features

Approvals:

- **BSI:** BS EN 41003, BS EN 60095 (BS 415), BS EN 60950 (BS 7002), Certificate number 7081 and 7402
- **FIMKO (SETI):** EN 60950, Certificate number 11027
- **Underwriters Laboratory (UL) 1577** recognized, file number E-76222 – Double Protection
- **CSA (C-UL) 1577** recognized file number E- 76222 - Double Protection
- **VDE 0884**, Certificate number 115667

VDE 0884 related features:

- Rated impulse voltage (transient overvoltage) $V_{IOTM} = 8$ kV peak
- Isolation test voltage (partial discharge test voltage) $V_{pd} = 1.6$ kV
- Rated isolation voltage (RMS includes DC) $V_{IOWM} = 600$ V_{RMS} (848 V peak)
- Rated recurring peak voltage (repetitive) $V_{IORM} = 600$ V_{RMS}

- Creepage current resistance according to VDE 0303/IEC 112
Comparative Tracking Index: CTI ≥ 175
- Thickness through insulation ≥ 0.75 mm
- Internal creepage distance > 4 mm

General features:

- CTR offered in 9 groups
- Isolation materials according to UL94-VO
- Pollution degree 2 (DIN/VDE 0110 / resp. IEC 664)
- Climatic classification 55/100/21 (IEC 68 part 1)
- Special construction: Therefore, extra low coupling capacity of typical 0.2 pF, high **Common Mode Rejection**
- Low temperature coefficient of CTR
- G = Leadform 10.16 mm; provides creepage distance > 8 mm, for TCET2100/ TCET4100 optional; suffix letter 'G' is not marked on the optocoupler
- Coupling System U



Absolute Maximum Ratings

Input (Emitter)

| Parameter | Test Conditions | Symbol | Value | Unit |
|-----------------------|---------------------------------|-----------|-------|------------------|
| Reverse voltage | | V_R | 6 | V |
| Forward current | | I_F | 60 | mA |
| Forward surge current | $t_p \leq 10 \mu\text{s}$ | I_{FSM} | 1.5 | A |
| Power dissipation | $T_{amb} \leq 25^\circ\text{C}$ | P_V | 100 | mW |
| Junction temperature | | T_j | 125 | $^\circ\text{C}$ |

Output (Detector)

| Parameter | Test Conditions | Symbol | Value | Unit |
|---------------------------|---------------------------------------|-----------|-------|------------------|
| Collector emitter voltage | | V_{CEO} | 70 | V |
| Emitter collector voltage | | V_{ECO} | 7 | V |
| Collector current | | I_C | 50 | mA |
| Collector peak current | $t_p/T = 0.5, t_p \leq 10 \text{ ms}$ | I_{CM} | 100 | mA |
| Power dissipation | $T_{amb} \leq 25^\circ\text{C}$ | P_V | 150 | mW |
| Junction temperature | | T_j | 125 | $^\circ\text{C}$ |

Coupler

| Parameter | Test Conditions | Symbol | Value | Unit |
|-------------------------------------|--------------------------------------|-----------|-------------|------------------|
| Isolation test voltage (RMS) | $t = 1 \text{ min}$ | V_{IO} | 5 | kV |
| Total power dissipation | $T_{amb} \leq 25^\circ\text{C}$ | P_{tot} | 250 | mW |
| Operating ambient temperature range | | T_{amb} | -40 to +100 | $^\circ\text{C}$ |
| Storage temperature range | | T_{stg} | -55 to +125 | $^\circ\text{C}$ |
| Soldering temperature | 2 mm from case $t \leq 10 \text{ s}$ | T_{sd} | 260 | $^\circ\text{C}$ |

TCET110.(G) up to TCET4100



Vishay Semiconductors

Electrical Characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Input (Emitter)

| Parameter | Test Conditions | Symbol | Min. | Typ. | Max. | Unit |
|----------------------|--|--------|------|------|------|------|
| Forward voltage | $I_F = \pm 50 \text{ mA}$ | V_F | | 1.25 | 1.6 | V |
| Junction capacitance | $V_R = 0 \text{ V}, f = 1 \text{ MHz}$ | C_j | | 50 | | pF |

Output (Detector)

| Parameter | Test Conditions | Symbol | Min. | Typ. | Max. | Unit |
|-----------------------------------|---|-----------|------|------|------|------|
| Collector emitter voltage | $I_C = 1 \text{ mA}$ | V_{CEO} | 70 | | | V |
| Emitter collector voltage | $I_E = 100 \mu\text{A}$ | V_{ECO} | 7 | | | V |
| Collector emitter cut-off current | $V_{CE} = 20 \text{ V}, I_f = 0, E = 0$ | I_{CEO} | | 10 | 100 | nA |

Coupler

| Parameter | Test Conditions | Symbol | Min. | Typ. | Max. | Unit |
|--------------------------------------|---|-------------|------|------|------|------|
| Collector emitter saturation voltage | $I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$ | V_{CEsat} | | | 0.3 | V |
| Cut-off frequency | $V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 100 \Omega$ | f_c | | 110 | | kHz |
| Coupling capacitance | $f = 1 \text{ MHz}$ | C_k | | 0.3 | | pF |

Current Transfer Ratio (CTR)

| Parameter | Test Conditions | Type | Symbol | Min. | Typ. | Max. | Unit |
|-----------|---|---------------------------------------|--------|------|------|------|------|
| I_C/I_F | $V_{CE} = 5 \text{ V}, I_F = 5 \text{ mA}$ | TCET1100(G)/ TCET2100/ TCET4100 | CTR | 0.50 | | 6.0 | |
| I_C/I_F | $V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}$ | TCET1101(G) | CTR | 0.40 | | 0.8 | |
| | | TCET1102(G) | CTR | 0.63 | | 1.25 | |
| | | TCET1103(G) | CTR | 1.0 | | 2.0 | |
| | | TCET1104(G) | CTR | 1.6 | | 3.2 | |
| I_C/I_F | $V_{CE} = 5 \text{ V}, I_F = 1 \text{ mA}$ | TCET1101(G) | CTR | 0.13 | 0.30 | | |
| | | TCET1102(G) | CTR | 0.22 | 0.45 | | |
| | | TCET1103(G) | CTR | 0.34 | 0.70 | | |
| | | TCET1104(G) | CTR | 0.56 | 0.90 | | |
| I_C/I_F | $V_{CE} = 5 \text{ V}, I_F = 5 \text{ mA}$ | TCET1105(G) | CTR | 0.5 | | 1.5 | |
| | | TCET1106(G) | CTR | 1.0 | | 3.0 | |
| | | TCET1107(G) | CTR | 0.8 | | 1.6 | |
| | | TCET1108(G) | CTR | 1.3 | | 2.6 | |
| | | TCET1109(G) | CTR | 2.0 | | 4.0 | |

Maximum Safety Ratings (according to VDE 0884) see figure 1

This device is used for protective separation against electrical shock only within the maximum safety ratings. This must be ensured by using protective circuits in the applications.

Input (Emitter)

| Parameters | Test Conditions | Symbol | Value | Unit |
|-----------------|-----------------|----------|-------|------|
| Forward current | | I_{si} | 130 | mA |

Output (Detector)

| Parameters | Test Conditions | Symbol | Value | Unit |
|-------------------|---------------------------|----------|-------|------|
| Power dissipation | $T_{amb} \leq 25^\circ C$ | P_{si} | 265 | mW |

Coupler

| Parameters | Test Conditions | Symbol | Value | Unit |
|-----------------------|-----------------|------------|-------|------------|
| Rated impulse voltage | | V_{IOTM} | 8 | kV |
| Safety temperature | | T_{si} | 150 | $^\circ C$ |

Insulation Rated Parameters (according to VDE 0884)

| Parameter | Test Conditions | Symbol | Min. | Typ. | Max. | Unit |
|---|--|------------|-----------|------|------|----------|
| Partial discharge test voltage – Routine test | 100%, $t_{test} = 1\text{ s}$ | V_{pd} | 1.6 | | | kV |
| Partial discharge test voltage – Lot test (sample test) | $t_{Tr} = 60\text{ s}$, $t_{test} = 10\text{ s}$, (see figure 2) | V_{IOTM} | 8 | | | kV |
| | | V_{pd} | 1.3 | | | kV |
| Insulation resistance | $V_{IO} = 500\text{ V}$ | R_{IO} | 10^{12} | | | Ω |
| | $V_{IO} = 500\text{ V}$, $T_{amb} = 100^\circ C$ | R_{IO} | 10^{11} | | | Ω |
| | $V_{IO} = 500\text{ V}$, $T_{amb} = 150^\circ C$ (construction test only) | R_{IO} | 10^9 | | | Ω |

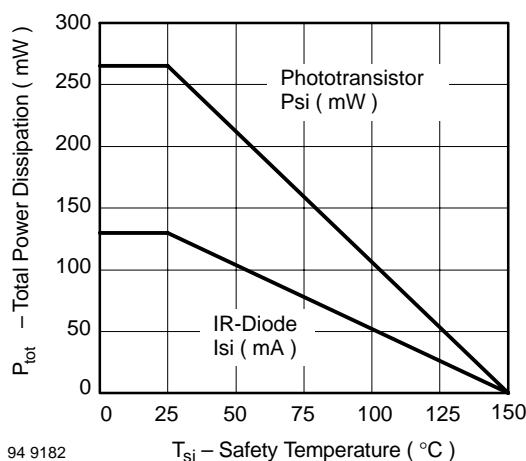


Figure 1. Derating diagram

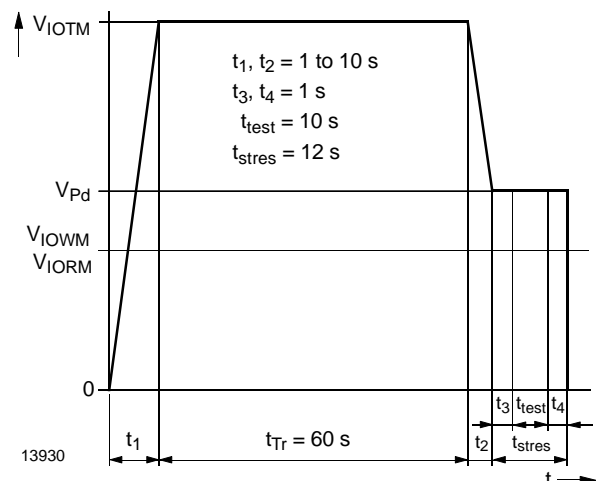


Figure 2. Test pulse diagram for sample test according to DIN VDE 0884

Switching Characteristics

| Parameter | Test Conditions | Symbol | Typ. | Unit |
|---------------|---|---|----------|---------------|
| Delay time | $V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$ (see figure 3) | t_d | 3.0 | μs |
| Rise time | | t_r | 3.0 | μs |
| Turn-on time | | t_{on} | 6.0 | μs |
| Storage time | | t_s | 0.3 | μs |
| Fall time | | t_f | 4.7 | μs |
| Turn-off time | | t_{off} | 5.0 | μs |
| Turn-on time | | $V_S = 5\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$ (see figure 4) | t_{on} | 9.0 |
| Turn-off time | t_{off} | | 10.0 | μs |

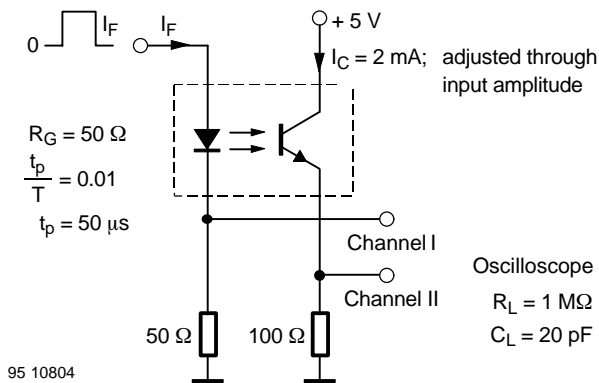


Figure 3. Test circuit, non-saturated operation

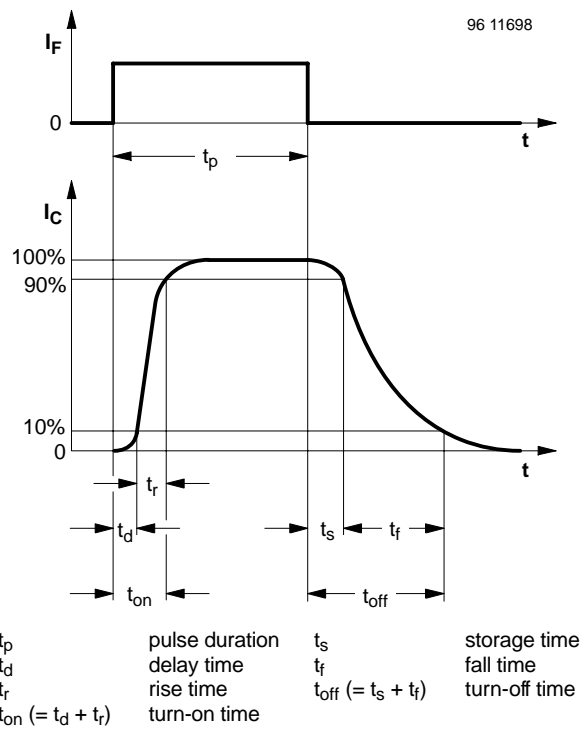


Figure 5. Switching times

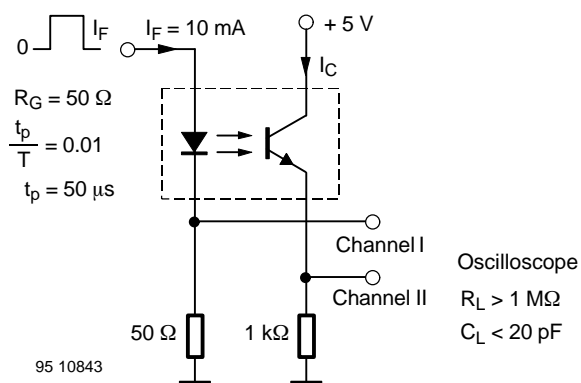


Figure 4. Test circuit, saturated operation

Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

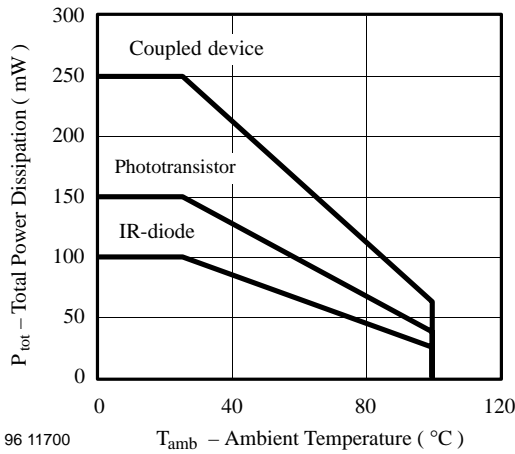


Figure 6. Total Power Dissipation vs. Ambient Temperature

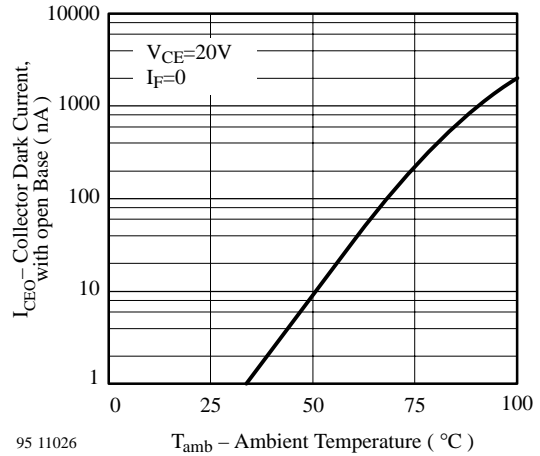


Figure 9. Collector Dark Current vs. Ambient Temperature

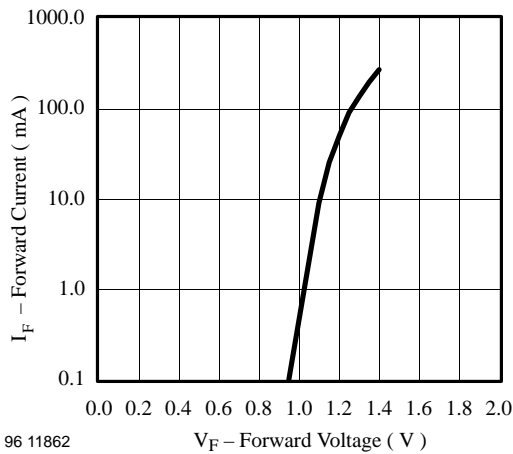


Figure 7. Forward Current vs. Forward Voltage

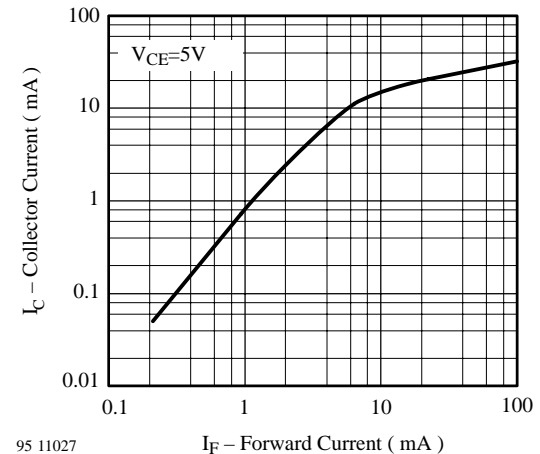


Figure 10. Collector Current vs. Forward Current

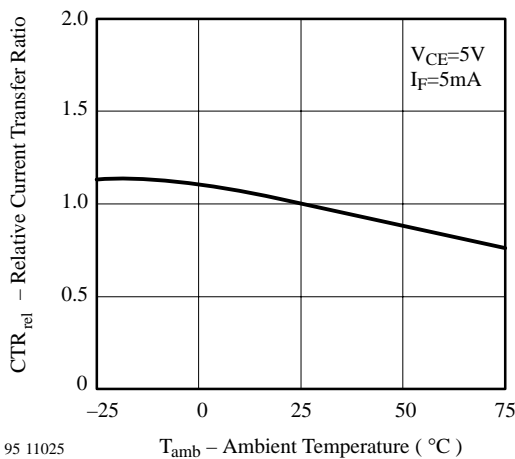


Figure 8. Relative Current Transfer Ratio vs. Ambient Temperature

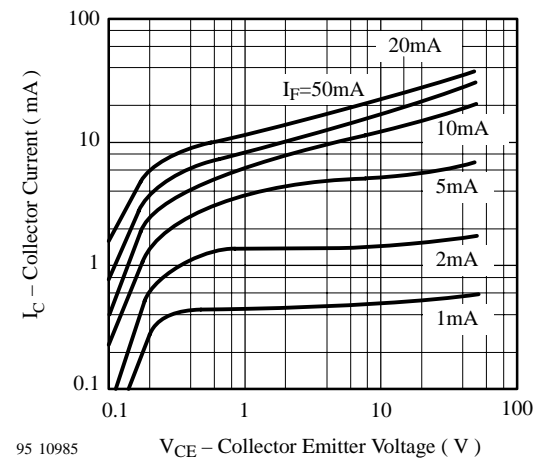
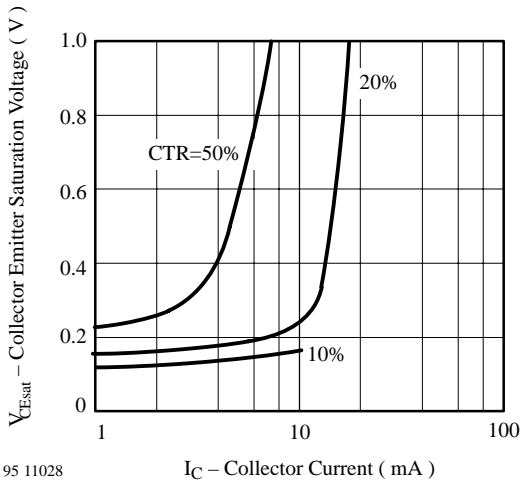
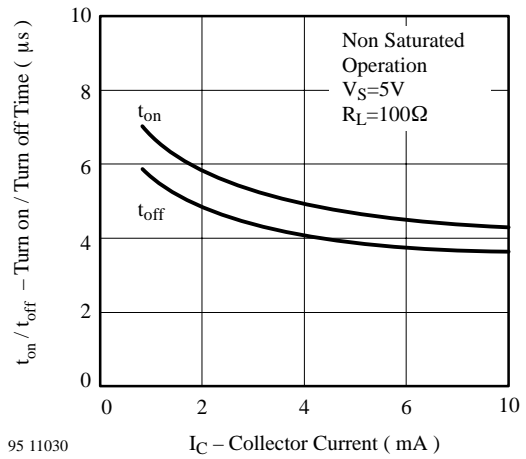


Figure 11. Collector Current vs. Collector Emitter Voltage



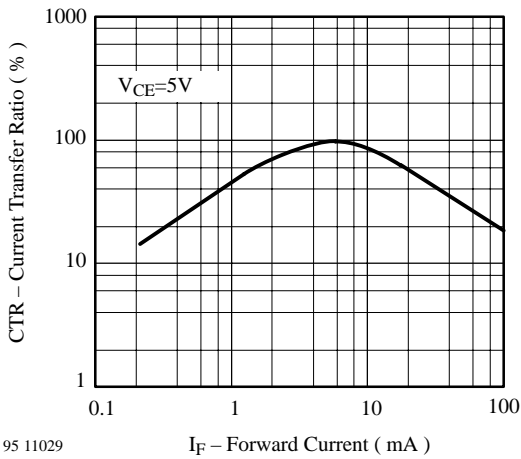
95 11028

Figure 12. Collector Emitter Saturation Voltage vs. Collector Current



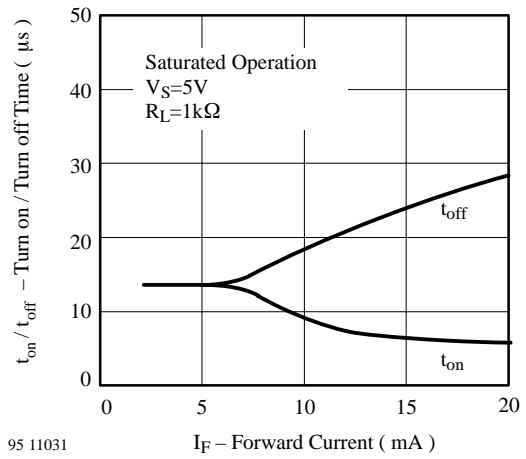
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Figure 14. Turn on / off Time vs. Collector Current



95 11029

Figure 13. Current Transfer Ratio vs. Forward Current



95 11031

Figure 15. Turn on / off Time vs. Forward Current

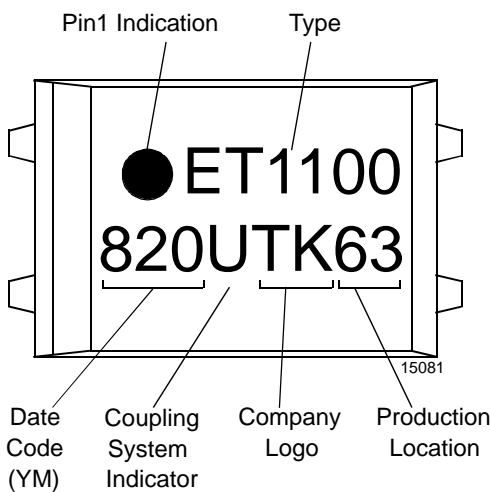


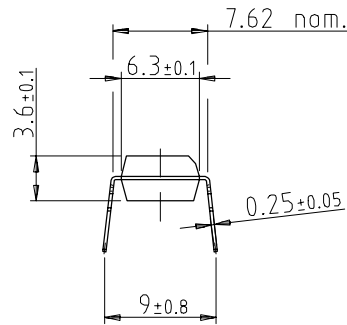
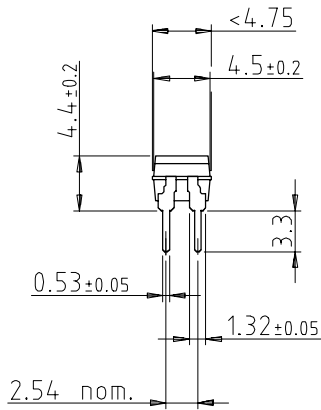
Figure 16. Marking example



TCET110.(G) up to TCET4100

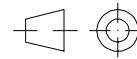
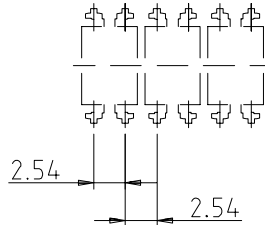
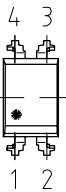
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Dimensions of TCET110. in mm



weight : ca 0.25g
 creepage distance : > 6mm
 air path : > 6mm
 after mounting on PC board

E.g.:
 special Features: endstackable
 to 2.54mm (.100") spacing

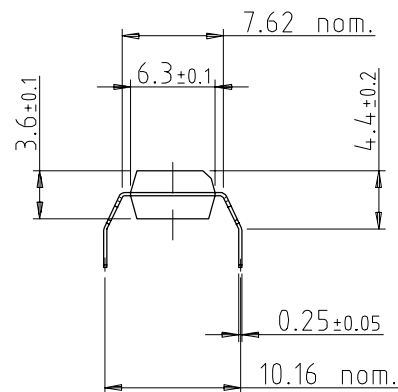
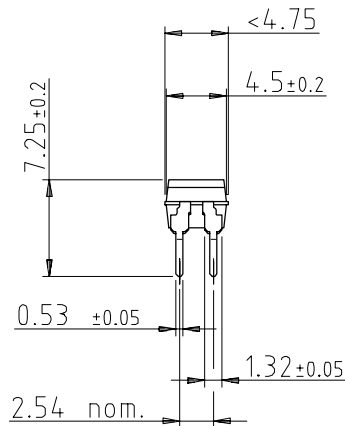


technical drawings
 according to DIN
 specifications

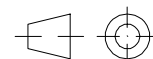
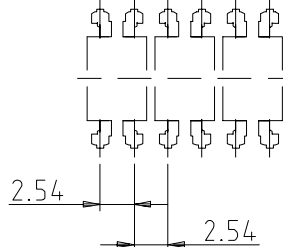
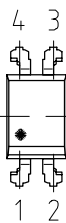
Drawing-No.: 6.544-5302.03-4
 Issue: 4; 02.06.99

14789

Dimensions of TCET110.G in mm



E.g.:
 special Features: endstackable
 to 2.54mm (.100") spacing



technical drawings
 according to DIN
 specifications

weight : ca 0.25g
 creepage distance : > 8mm
 air path : > 8mm
 after mounting on PC board

Drawing-No.: 6.544-5303.03-4
 Issue: 3; 02.06.99

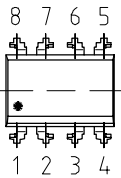
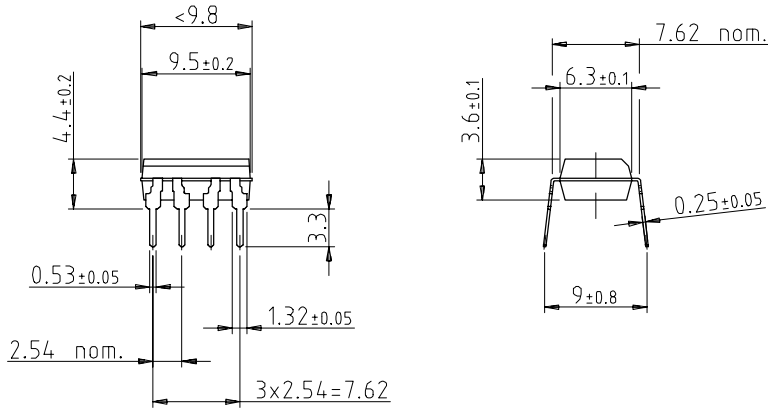
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TCET110.(G) up to TCET4100

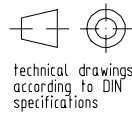
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Dimensions of TCET2100 in mm



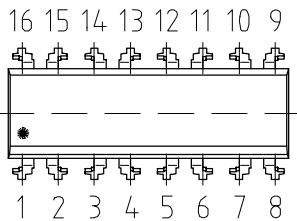
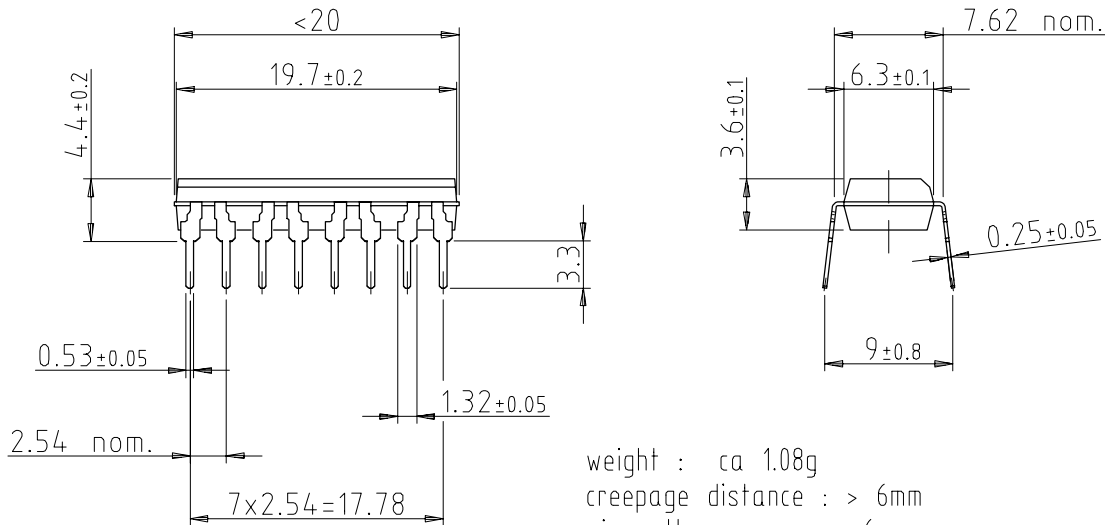
weight : ca 0.55g
 creepage distance : > 6mm
 air path : > 6mm
 after mounting on PC board



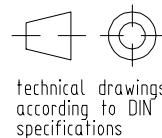
Drawing-No.: 6.544-5302.02-4
 Issue: 4; 02.06.99

14784

Dimensions of TCET4100 in mm



weight : ca 1.08g
 creepage distance : > 6mm
 air path : > 6mm
 after mounting on PC board



Drawing-No.: 6.544-5302.01-4
 Issue: 4; 02.06.99

14783



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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